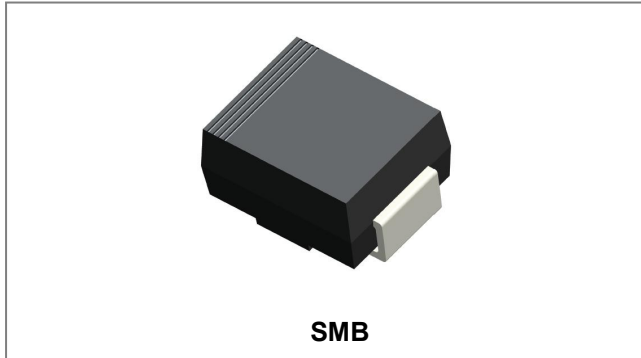


SK26 SCHOTTKY RECTIFIER



Features

- Schottky Barrier Chip
- Guard Ring Die Construction for Transient Protection
- High Current Capability
- Low Power Loss, High Efficiency
- High Surge Current Capability
- For Use in Low Voltage, High Frequency Inverters, Free Wheeling, and Polarity Protection Applications
- This is a Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Circuit Diagram



Mechanical Data

- Case: Low Profile Molded plastic
- Terminals: Plated leads solderable per MIL-STD-750, Method 2026
- Polarity: Color band or cathode Notch
- Mounting Position: Any
- Weight: 0.09grams(approx)

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	-	60	V
Average Rectified Forward Current	$I_{F(AV)}$	50% duty cycle @ $T_A=55^\circ\text{C}$, rectangular wave form	2	A
Peak One Cycle Non-Repetitive Surge Current	I_{FSM}	8.3ms, Half Sine pulse, $T_c = 25^\circ\text{C}$	50	A

Electrical Characteristics:

Characteristics	Symbol	Condition	Typ.	Max.	Units
Forward Voltage Drop*	V_{F1}	@ 2A, Pulse, $T_J = 25^\circ\text{C}$	0.58	0.70	V
Reverse Current*	I_{R1}	@ $V_R = \text{rated } V_R, T_J = 25^\circ\text{C}$	0.01	0.5	mA
	I_{R2}	@ $V_R = \text{rated } V_R, T_J = 100^\circ\text{C}$	1	20	mA
Junction Capacitance	C_T	@ $V_R = 5\text{V}, T_c = 25^\circ\text{C}, f_{SIG} = 1\text{MHz}$	80	400	pF
Series Inductance	L_S	Measured lead to lead 5 mm from package body	8.0	-	nH
Voltage Rate of Change	dv/dt	-	-	10,000	V/ μs

* Pulse width < 300 μs , duty cycle < 2%

Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	T_J	-	-55 to +150	$^{\circ}\text{C}$
Storage Temperature	T_{stg}	-	-55 to +150	$^{\circ}\text{C}$
Typical Thermal Resistance Junction to Ambient	$R_{\theta\text{JA}}$	DC operation	75	$^{\circ}\text{C}/\text{W}$
Approximate Weight	wt	-	0.09	g

Ratings and Characteristics Curves

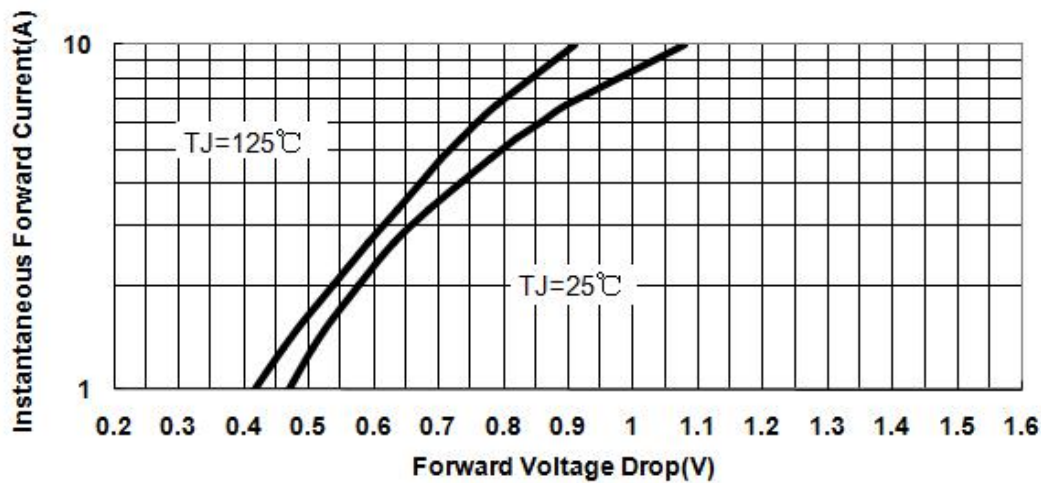


Fig.1-Typical Forward Voltage Drop Characteristics

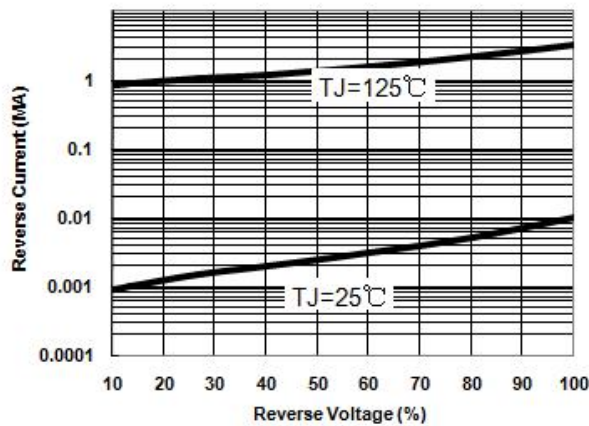


Fig.2-Typical Values Of Reverse Current VS.Reverse Voltage

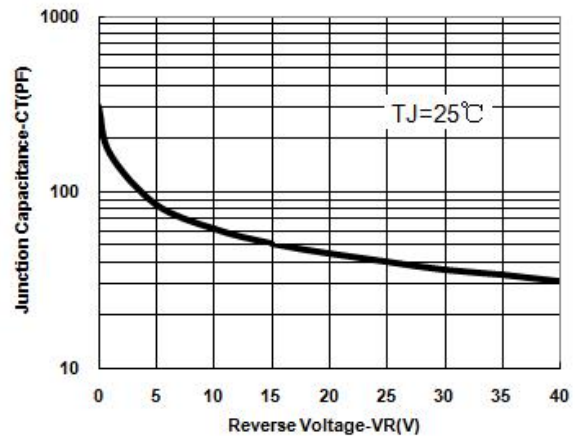
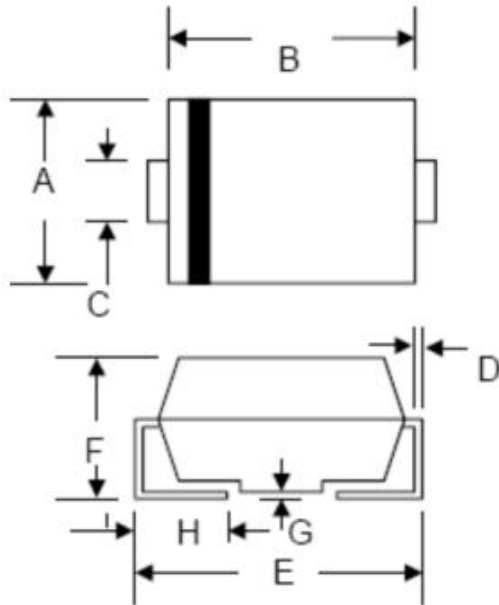


Fig.3-Typical Junction Capacitance Vs.Reverse Voltage

Mechanical Dimensions SMB



SYMBOL	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	3.30	3.94	0.130	0.155
B	4.06	4.70	0.160	0.185
C	1.80	2.20	0.071	0.087
D	0.152	0.305	0.006	0.012
E	4.80	5.59	0.189	0.220
F	2.10	2.60	0.083	0.102
G	0.051	0.203	0.002	0.008
H	0.76	1.52	0.030	0.060

Ordering Information

Device	Package	Shipping
SK26	SMB	3000pcs / reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

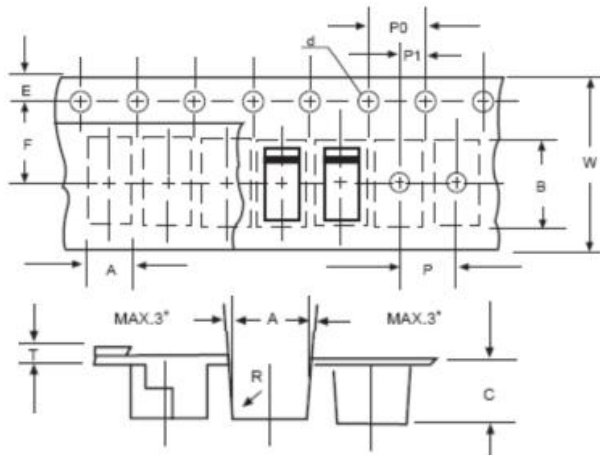
Marking Diagram



First row: Part Number
Second row: YYWWL
YY is the manufacture year,
WW is the manufacture week code,
L is the wafer's Lot Number

Cautions: Molding resin
Epoxy resin UL:94V-0

Carrier Tape Specification SMB



SYMBOL	Millimeters	
	Min.	Max.
A	2.97	3.17
B	5.70	5.90
C	2.32	2.52
d	1.40	1.60
E	1.40	1.60
F	5.60	5.70
P	3.90	4.10
P0	3.90	4.10
P1	1.90	2.10
T	0.25	0.35
W	11.80	12.20

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